

FS10AS-2

High-Speed Switching Use Nch Power MOS FET

REJ03G0244-0200 Rev.2.00 Nov 21, 2006

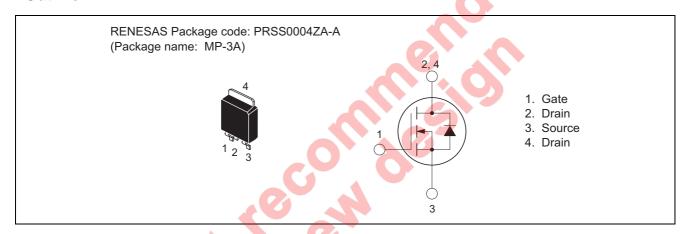
Features

 $\begin{array}{ll} \bullet & Drive\ voltage: 10\ V \\ \bullet & V_{DSS}: 100\ V \\ \bullet & r_{DS(ON)\ (max)}: 0.23\ \Omega \end{array}$

• I_D: 10 A

• Recovery Time of the Integrated Fast Recovery Diode (TYP.): 100 ns

Outline



Applications

Motor control, lamp control, solenoid control, DC-DC converters, etc.

Maximum Ratings

 $(Tc = 25^{\circ}C)$

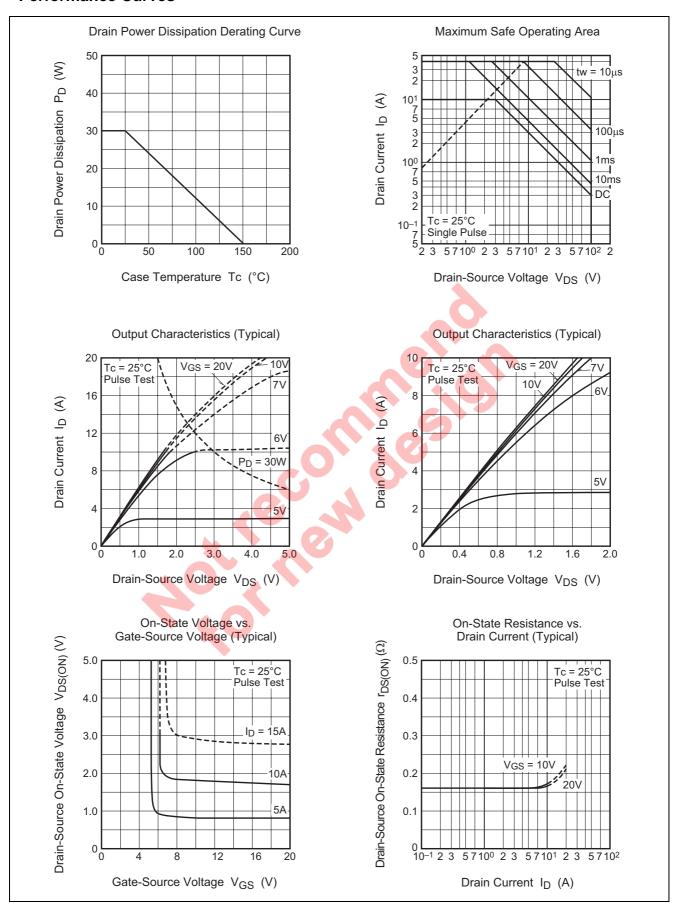
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V _{DSS}	100	V	V _{GS} = 0 V
Gate-source voltage	V _{GSS}	±20	V	V _{DS} = 0 V
Drain current	I _D	10	А	
Drain current (Pulsed)	I _{DM}	40	А	
Avalanche current (Pulsed)	I _{DA}	10	А	L = 100 μH
Source current	Is	10	А	
Source current (Pulsed)	I _{SM}	40	А	
Maximum power dissipation	P _D	30	W	
Channel temperature	Tch	- 55 to +150	°C	
Storage temperature	Tstg	- 55 to +150	°C	
Mass	_	0.32	g	Typical value

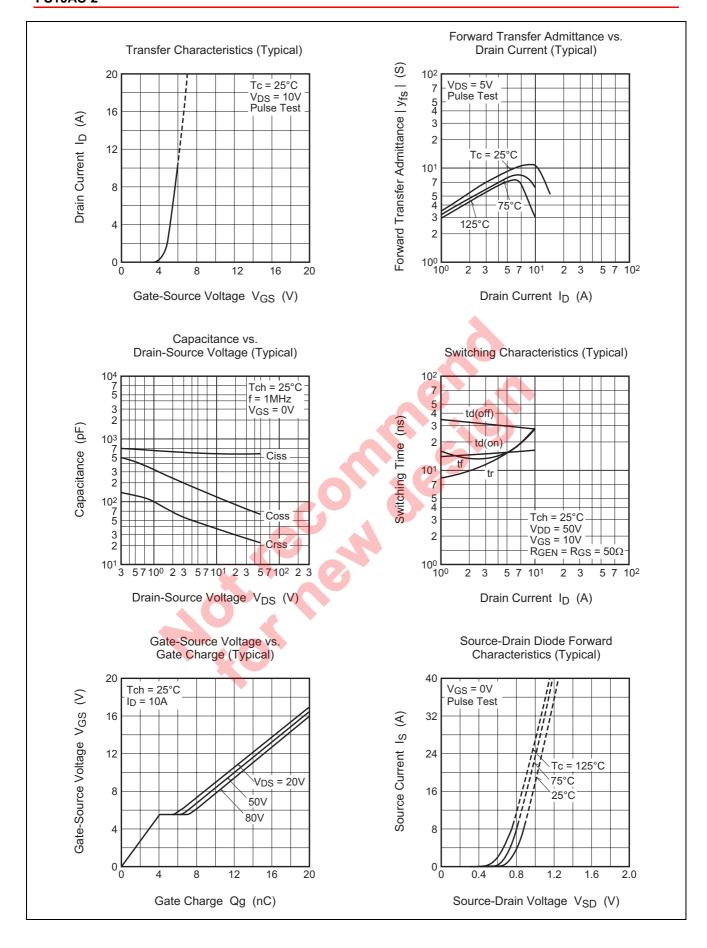
Electrical Characteristics

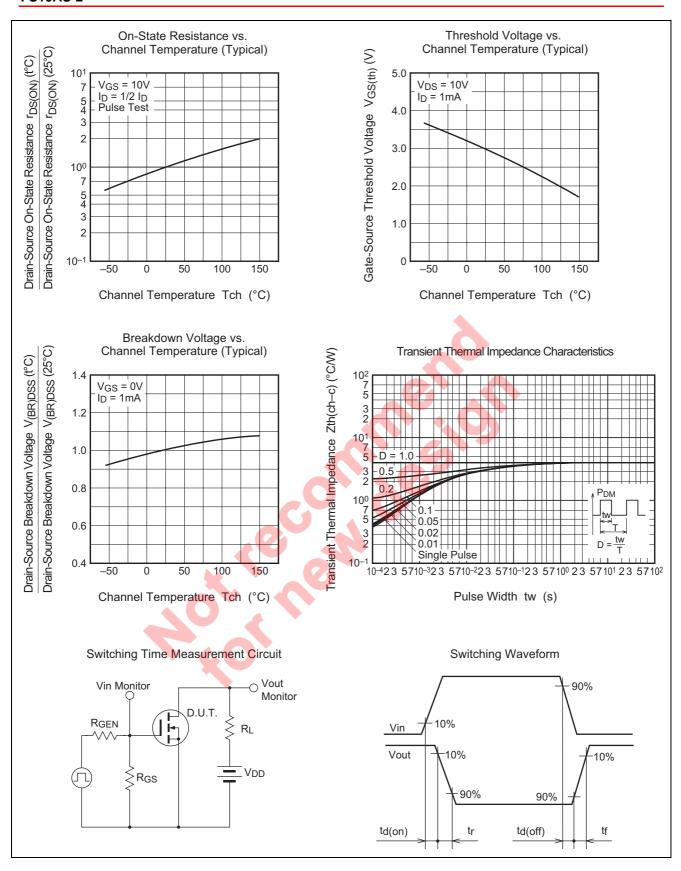
 $(Tch = 25^{\circ}C)$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions
Drain-source breakdown voltage	V _{(BR)DSS}	100	—	_	V	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$
Gate-source leakage current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Drain-source leakage current	I _{DSS}	_	_	0.1	mA	V _{DS} = 100 V, V _{GS} = 0 V
Gate-source threshold voltage	V _{GS(th)}	2.0	3.0	4.0	V	I _D = 1 mA, V _{DS} = 10 V
Drain-source on-state resistance	r _{DS(ON)}	_	0.16	0.23	Ω	I _D = 5 A, V _{GS} = 10 V
Drain-source on-state voltage	V _{DS(ON)}	_	0.80	1.15	V	$I_D = 5 \text{ A}, V_{GS} = 10 \text{ V}$
Forward transfer admittance	y _{fs}	_	9.0	_	S	I _D = 5 A, V _{DS} = 5 V
Input capacitance	Ciss	_	600	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$
Output capacitance	Coss	_	125	_	pF	f = 1MHz
Reverse transfer capacitance	Crss	_	40	_	pF	
Turn-on delay time	t _{d(on)}	_	18	_	ns	$V_{DD} = 50 \text{ V}, I_D = 5 \text{ A},$
Rise time	t _r	_	20	_	ns	V _{GS} = 10 V,
Turn-off delay time	t _{d(off)}	_	30	_	ns	$R_{GEN} = R_{GS} = 50 \Omega$
Fall time	t _f	_	18	_	ns	
Source-drain voltage	V _{SD}	_	1.0	1.5	V	I _S = 5 A, V _{GS} = 0 V
Thermal resistance	Rth(ch-c)	_	_	4.17	°C/W	Channel to case
Reverse recovery time	t _{rr}	_	100		ns	$I_S = 10 \text{ A}, \text{ dis/dt} = -100 \text{ A/}\mu\text{s}$
Hot lecondes to						

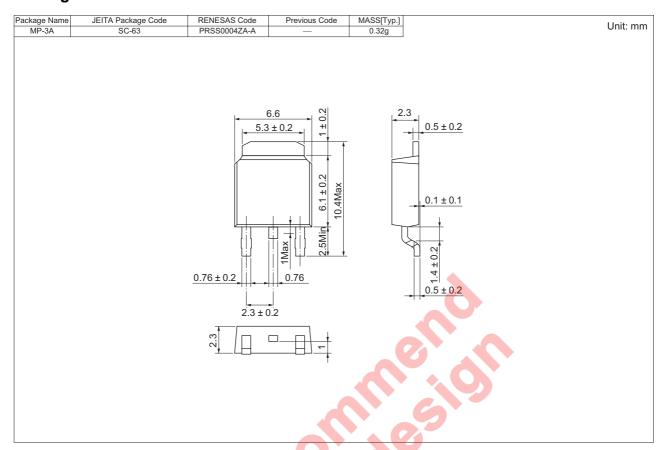
Performance Curves







Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FS10AS-2-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	FS10AS-2

Note: Please confirm the specification about the shipping in detail.

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- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

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